

## UNISONIC TECHNOLOGIES CO., LTD

UT3400 Power MOSFET

SOT-23 (EIAJ SC-59)

SOT-23-3 (JEDEC TO-236)

QW-R502-371.C

# 5.8A, 30V N-CHANNEL ENHANCEMENT MODE POWER MOSFET

#### **■ DESCRIPTION**

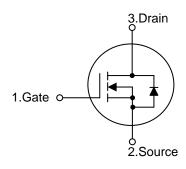
The UTC **UT3400** is an N-ch enhancement MOSFET providing the customers with perfect  $R_{DS(ON)}$  and low gate charge. This device can be operated with 2.5V low gate voltage.

The UTC **UT3400** is optimized for applications, such as a load switch or in PWM.

#### **■ FEATURES**

\*  $R_{DS(ON)} \le 28 \text{ m}\Omega$  @  $V_{GS}=10\text{V}$ ,  $I_D=5.8\text{A}$   $R_{DS(ON)} \le 33 \text{ m}\Omega$  @  $V_{GS}=4.5\text{V}$ ,  $I_D=5.0\text{A}$   $R_{DS(ON)} \le 52 \text{ m}\Omega$  @  $V_{GS}=2.5\text{V}$ ,  $I_D=4.0\text{A}$ 

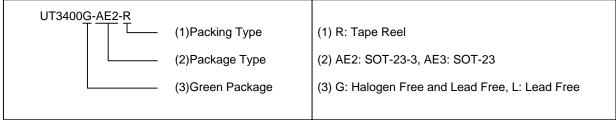
#### ■ SYMBOL



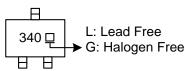
#### ■ ORDERING INFORMATION

Ordering Number		Deelsess	Pin Assignment			Dankina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UT3400L-AE2-R	UT3400G-AE2-R	SOT-23-3	G	S	D	Tape Reel	
UT3400L-AE3-R	UT3400G-AE3-R	SOT-23	G	S	D	Tape Reel	

Note: Pin Assignment: G: Gate S: Source D: Drain



#### MARKING



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UT3400 Power MOSFET

#### ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	±12	V
Continuous Drain Current	I <sub>D</sub>	5.8	Α
Pulsed Drain Current (Note 2)	I <sub>DM</sub>	30	Α
Power Dissipation	P <sub>D</sub>	1.4	W
Junction Temperature	TJ	+150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. Pulse width ≤300µs, duty cycle≤0.5%.

#### **■ THERMAL DATA**

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient (Note)	$\theta_{JA}$		85	125	°C/W

Note: Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board with 2oz.

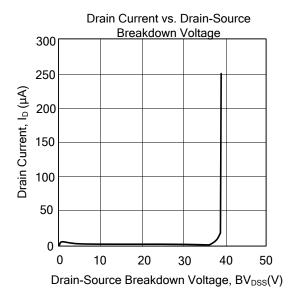
#### ■ **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub>=25°C, unless otherwise specified)

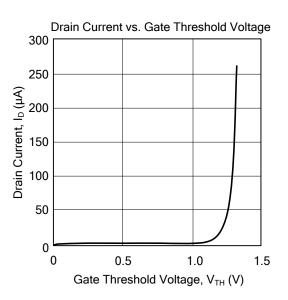
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS} = 0V, I_D = 250 \mu A$	30			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V			1	μΑ
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 12V, V_{DS} = 0V$			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.7	1.1	1.4	V
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> =5V, V <sub>GS</sub> =4.5V	30			Α
	R <sub>DS(ON)</sub>	$V_{GS} = 10V, I_D = 5.8A$		22.8	28	mΩ
Drain to Source On-state Resistance		$V_{GS} = 4.5V, I_D = 5A$		27.3	33	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4 A		43.3	52	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C <sub>ISS</sub>			823		pF
Output Capacitance	Coss	$V_{DS} = 15V$ , $V_{GS} = 0V$ , $f = 1MHz$		99		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			77		pF
Gate Resistance	$R_{G}$	$V_{GS}=0V$ , $V_{DS}=0V$ , $f=1MHz$		1.2		Ω
SWITCHING PARAMETERS						
Total Gate Charge	$Q_{G}$			9.7		nC
Gate Source Charge	Q <sub>GS</sub>	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 5.8A$		1.6		nC
Gate Drain Charge	$Q_{GD}$			3.1		nC
Turn-ON Delay Time	t <sub>D(ON)</sub>			5.5		ns
Turn-ON Rise Time	t <sub>R</sub>	$V_{GS} = 10V, V_{DS} = 15V$		5.1		ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>	$R_L = 2.7\Omega, R_{GEN} = 6\Omega$		37		ns
Turn-OFF Fall-Time	t <sub>F</sub>			4.2		ns
SOURCE- DRAIN DIODE RATINGS AND CHA	ARACTERIS	STICS				
Diode Continuous Forward Current (Note 1)	Is				2.5	Α
Drain-Source Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.71	1	V
Reverse Recovery Time	t <sub>rr</sub>			16		ns
Reverse Recovery Charge	Qrr	I <sub>F</sub> =5A, dl/dt=100A/μs		8.9		nC

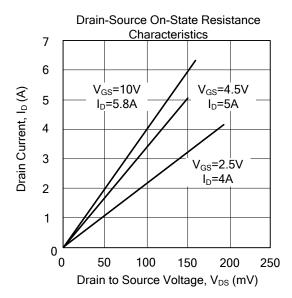
Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

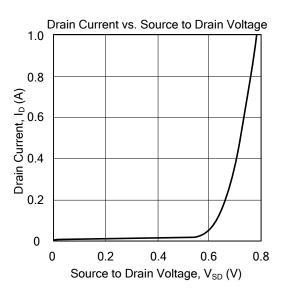
2. Pulse width ≤300µs, duty cycle≤0.5%.

#### **■ TYPICAL CHARACTERISTICS**









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